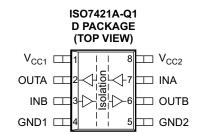


LOW-POWER DUAL DIGITAL ISOLATORS

FEATURES

- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
 - Device Temperature Grade 1: –40°C to 125°C Ambient Operating Temperature Range
 - Device HBM ESD Classification Level H3A
 - Device CDM ESD Classification Level C5
- High Signaling Rate: 50 Mbps
- Low Power Consumption
- Low Propagation Delay 9 ns (Typical)
- Low Skew 300 ps (Typical)
- 4-kVpeak Maximum Isolation, 2.5 kVrms per UL 1577, IEC/VDE and CSA Approved, IEC 60950-1, IEC 61010-1 End Equipment Standards Approved. All Approvals Pending.
- 50 kV/µs Transient Immunity (Typical)
- Over 25-Year Isolation Integrity at Rated Voltage
- Operates From 3-V to 5.5-V Supply and Logic Levels



DESCRIPTION

The ISO7421A-Q1 provides galvanic isolation up to 2.5 kVrms for 1 minute per UL. This digital isolator has two isolated channels with bidirectional channel configuration. Each isolation channel has a logic input and output buffer separated by a silicon dioxide (SiO₂) insulation barrier. Used in conjunction with isolated power supplies, these devices prevent noise currents on a data bus or other circuit from entering the local ground and interfering with or damaging sensitive circuitry.

The devices have TTL input thresholds and require two supply voltages from 3 V to 5.5 V, or any combination. All inputs are 5-V tolerant when supplied from a 3-V supply.

ORDERING INFORMATION⁽¹⁾

T _A	PACK	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 125°C	SOIC - D	Reel of 2500	ISO7421AQDRQ1	7421AQ

⁽¹⁾ For the most-current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

PIN FUNCTIONS

P	PIN	1/0	DECORIDATION	
NAME	NO.	1/0	DESCRIPTION	
GND1	4	_	Ground connection for V _{CC1}	
GND2	5	_	Ground connection for V _{CC2}	
INA	7	I	Input, channel A	
INB	3	I	Input, channel B	
OUTA	2	0	Output, channel A	
OUTB	6	0	Output, channel B	
V _{CC1}	1	_	Power supply, V _{CC1}	
V _{CC2}	8	-	Power supply, V _{CC2}	

Table 1. FUNCTION TABLE(1)

INPUT SIDE VCC	OUTPUT SIDE VCC	INPUT IN	OUTPUT OUT
		Н	Н
PU	PU	L	L
		Open	Н
PD	PU	Х	Н

(1) PU = Powered up ($V_{CC} \ge 3$ V), PD = Powered down ($V_{CC} \le 2.4$ V), X = Irrelevant, H = High level, L = Low level

ABSOLUTE MAXIMUM RATINGS(1)

V_{CC}	CC Supply voltage (2), V _{CC1} , V _{CC2}				
V_{I}	Voltage at IN, OUT			–0.5 V to 6 V	
Io	Output current	±15 mA			
		Human-body model (HBM) AEC-Q100 Classification Level H3A		4 kV	
ESD	Electrostatic discharge	Charged-device model (CDM) AEC-Q100 Classification Level C5	All pins	1.5 kV	
	discriarge	Machine model (MM)		200 V	
$T_{J(Max)}$	J _(Max) Maximum junction temperature				

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.

RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
V _{CC1} , V _{CC2}	Supply voltage	3		5.5	V
I _{OH}	High-level output current	-4			mA
I _{OL}	Low-level output current			4	mA
V_{IH}	High-level input voltage	2		V_{CC}	V
V_{IL}	Low-level input voltage	0		8.0	V
T _A	Operating temperature	-40		125	°C



 $V_{CC1} = V_{CC2} = 5 \text{ V } \pm 10\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
.,	High lavel autout valtage		I _{OH} = -4 mA, see Figure 1	V _{CC} - 0.8	4.6		V
V_{OH}	High-level output voltage	I _{OH} I _{OL} I _{OL} IN 1 IN 2	$I_{OH} = -20 \mu A$, see Figure 1	V _{CC} - 0.1	5		V
.,	Landard advisor		I _{OL} = 4 mA, see Figure 1		0.2	0.4	
V_{OL}	Low-level output voltage	el output voltage el output voltage eshold voltage hysteresis el input current el input current pacitance to ground n-mode transient immunity ENT (All inputs switching with square DC to 1 Mb 10 Mbps current for V _{CC1} and V _{CC2}	I _{OL} = 20 μA, see Figure 1		0	0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis	02 1			400		mV
I _{IH}	High-level input current		IN Grand O.V. and V.			10	μΑ
I _{IL}	Low-level input current		IN from 0 V or V _{CC}				μΑ
C _I	Input capacitance to ground		IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		1.2		pF
CMTI	Common-mode transient immunity		V _I = V _{CC} or 0 V, see Figure 3	25	50		kV/µs
SUPPL	Y CURRENT (All inputs switching	with square v	vave clock signal for dynamic I _{CC} m	neasurement)		,	
I _{CC1}		DO (- 4 M)	DC Input: V _I = V _{CC} or 0 V		2.3	3.6	
I _{CC2}		DC to 1 Mbp	AC Input: $C_L = 15 \text{ pF}$		2.3	3.6	
I _{CC1}		40 Mb			2.9	4.5	
I _{CC2}		10 Mbps			2.9	4.5	
I _{CC1}	Supply current for V_{CC1} and V_{CC2}	05 Mb	0 45 75		4.3	6	mA
I _{CC2}		25 IVIDPS	$C_L = 15 pF$		4.3	6	
I _{CC1}		50.14			6	9.1	
I _{CC2}		50 Mbps			6	9.1	

SWITCHING CHARACTERISTICS

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1		9	14	ns
PWD ⁽¹⁾	Pulse duration distortion t _{PHL} - t _{PLH}			0.3	3.7	ns
t _{sk(pp)}	Part-to-part skew time				4.9	ns
t _{sk(o)}	Channel-to-channel output skew time				3.6	ns
t _r	Output signal rise time	See Figure 1		1		ns
t _f	Output signal fall time			1		ns
t _{fs}	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t _{ui}	Input pulse duration		7			ns
1 / t _{ui}	Signaling rate		0		50	Mbps

⁽¹⁾ Also known as pulse skew



 $V_{CC1} = 5 \text{ V} \pm 10\%$, $V_{CC2} = 3.3 \text{ V} \pm 10\%$, $T_A = -40^{\circ}\text{C}$ to 125°C

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
.,	Libe level autout valtage	I _{OH} = -4 m	A, see Figure 1, 5-V side	V _{CC} - 0.8			V
V _{OH}	High-level output voltage	I _{OH} = -20	JA, see Figure 1	V _{CC} - 0.1			V
\ /	Lauriana antant nata aa	I _{OL} = 4 mA	, see Figure 1			0.4	V
V _{OL}	Low-level output voltage	$I_{OL} = 20 \mu$	A, see Figure 1			0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	IN from O	/ or \/			10	μΑ
I _{IL}	Low-level input current	IN from 0 \	7 OI V _{CC}	-10			μΑ
C _I	Input capacitance to ground	IN at V _{CC} ,	V _I = 0.4 sin (4E6πt)		1.2		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ o	r 0 V, see Figure 3	25	40		kV/μs
SUPPL	Y CURRENT (All inputs switching w	ith square wave	clock signal for dynamic I _{CC} mea	surement)			
I _{CC1}		DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V		2.3	3.6	
I _{CC2}		DC to 1 Mbps	AC Input: C _L = 15 pF		1.8	2.8	
I _{CC1}		10 Mbna			2.9	4.5	
I _{CC2}	Cumply ourrent for V	10 Mbps			2.2	3.2	mA
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	OF Mhno	C 15 pF		4.3	6	
I _{CC2}		25 Mbps	C _L = 15 pF		2.8	4.1	
I _{CC1}		50 Mbps			6	9.1	
I _{CC2}		Squivi oc			3.8	5.8	

SWITCHING CHARACTERISTICS

 $V_{CC1} = 5 \text{ V } \pm 10\%, V_{CC2} = 3.3 \text{ V } \pm 10\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1		10	17	ns
PWD ⁽¹⁾	Pulse duration distortion t _{PHL} - t _{PLH}			0.5	5.6	ns
t _{sk(pp)}	Part-to-part skew time				6.3	ns
t _{sk(o)}	Channel-to-channel output skew time				4	ns
t _r	Output signal rise time	See Figure 1		2		ns
t _f	Output signal fall time			2		ns
t _{fS}	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t _{ui}	Input pulse duration		7			ns
1 / t _{ui}	Signaling rate		0		50	Mbps

⁽¹⁾ Also known as pulse skew



 $V_{CC1} = 3.3 \text{ V} \pm 10\%, V_{CC2} = 5 \text{ V} \pm 10\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	Т	EST CONDITIONS	MIN	TYP	MAX	UNIT
V	Lligh lovel output voltage	$I_{OH} = -4 \text{ mA}, \text{ s}$	I _{OH} = -4 mA, see Figure 1, 3.3-V side				V
V_{OH}	High-level output voltage	$I_{OH} = -20 \mu A$	see Figure 1	V _{CC} - 0.1			V
W	Lave lavel autout valta as	I _{OL} = 4 mA, se	e Figure 1			0.4	
V_{OL}	Low-level output voltage	$I_{OL} = 20 \mu A, se$	ee Figure 1		0	0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INI frame O V an	V			10	μΑ
I _{IL}	Low-level input current	IN from 0 V or	v _{CC}	-10			μΑ
Cı	Input capacitance to ground	IN at V _{CC} , V _I =	IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 \	V _I = V _{CC} or 0 V, see Figure 3		40		kV/μs
SUPPL	Y CURRENT (All inputs switching witl	n square wave cloc	k signal for dynamic I _{CC} meas	urement)			
I _{CC1}		DC to 4 Mbns	DC Input: V _I = V _{CC} or 0 V		1.8	2.8	
I _{CC2}		DC to 1 Mbps	AC Input: $C_L = 15 pF$		2.3	3.6	
I _{CC1}		40 Mb			2.2	3.2	
I _{CC2}	Our also suggest for M. and M.	10 Mbps			2.9	4.5	^
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	05.14	0 45 5		2.8	4.1	mA
I _{CC2}		25 Mbps	$C_L = 15 pF$		4.3	6	
I _{CC1}		50 Mhaa			3.8	5.8	
I _{CC2}		50 Mbps			6	9.1	

SWITCHING CHARACTERISTICS

 $V_{CC1} = 3.3 \text{ V} \pm 10\%, V_{CC2} = 5 \text{ V} \pm 10\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1		10	17	ns
PWD ⁽¹⁾	Pulse duration distortion t _{PHL} - t _{PLH}			0.5	4	ns
t _{sk(pp)}	Part-to-part skew time				8.5	ns
t _{sk(o)}	Channel-to-channel output skew time				4	ns
t _r	Output signal rise time	See Figure 1		2		ns
t _f	Output signal fall time			2		ns
t _{fs}	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t _{ui}	Input pulse duration		7			ns
1 / t _{ui}	Signaling rate		0		50	Mbps

⁽¹⁾ Also known as pulse skew



 $V_{CC1} = V_{CC2} = 3.3 \text{ V } \pm 5\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	TE	ST CONDITIONS	MIN	TYP	MAX	UNIT
.,	High lavel autout valtage	$I_{OH} = -4$ mA, see	e Figure 1	V _{CC} - 0.4	3		V
V _{OH}	High-level output voltage	$I_{OH} = -20 \mu A$, se	ee Figure 1	V _{CC} - 0.1	3.3		V
.,	Laur laural autout valta ea	I _{OL} = 4 mA, see	Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage	$I_{OL} = 20 \mu A$, see	Figure 1		0	0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	IN from O V or V				10	μΑ
I _{IL}	Low-level input current	IN from 0 V or V	CC	-10			μΑ
C _I	Input capacitance to ground	IN at V_{CC} , $V_I = 0$	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V,	V _I = V _{CC} or 0 V, see Figure 3.		40		kV/µs
SUPPL	Y CURRENT (All inputs switching with	square wave clock	signal for dynamic I _{CC} measu	rement)			
I _{CC1}		DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V		1.8	2.8	
I _{CC2}		DC to 1 Mbps	AC Input: C _L = 15 pF		1.8	2.8	
I _{CC1}		10 Mbps			2.2	3.2	
I_{CC2}	Cupply current for \/ and \/	10 Mbps			2.2	3.2	A
I _{CC1}	Supply current for V _{CC1} and V _{CC2}	25 Mbno	C 45 pF		2.8	4.1	mA
I _{CC2}		25 Mbps	C _L = 15 pF		2.8	4.1	
I _{CC1}		50 Mbps			3.8	5.8	
I _{CC2}		ou minhe			3.8	5.8	

SWITCHING CHARACTERISTICS

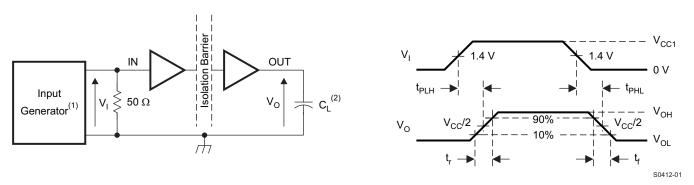
 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 5\%, T_A = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1		12	20	ns
PWD ⁽¹⁾	Pulse duration distortion t _{PHL} - t _{PLH}			1	5	ns
t _{sk(pp)}	Part-to-part skew time				6.8	ns
t _{sk(o)}	Channel-to-channel output skew time				5.5	ns
t _r	Output signal rise time	Con Figure 4		2		ns
t _f	Output signal fall time	See Figure 1		2		ns
t _{fs}	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t _{ui}	Input pulse duration		7			ns
1 / t _{ui}	Signaling rate		0		50	Mbps

(1) Also known as pulse skew

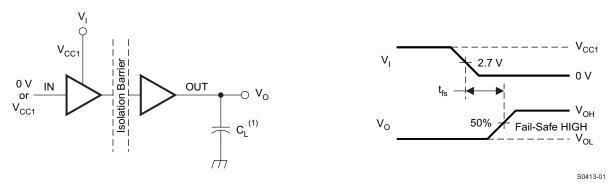


PARAMETER MEASUREMENT INFORMATION



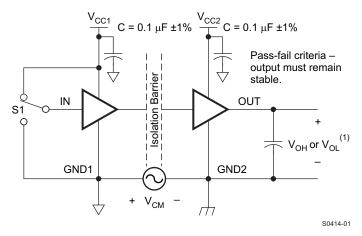
- (1) The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns, $t_f \leq$ 50 Ω .
- (2) $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms



(1) $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 2. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



(1) $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 3. Common-Mode Transient Immunity Test Circuit



DEVICE INFORMATION

PACKAGE CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4.8			mm
L(I02)	Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4.3			mm
СТІ	Tracking resistance (comparative tracking index)	DIN IEC 60112 / VDE 0303 Part 1	>175			V
	Minimum internal gap (internal clearance)	Distance through the insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, V_{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device, T_A < 100°C		>10 ¹²		Ω
		Input to output		>10 ¹¹		Ω
C _{IO}	Barrier capacitance, input to output	$V_1 = 0.4 \sin (4E6\pi t)$		1		pF

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

INSULATION CHARACTERISTICS(1)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	SPECIFICATION	UNIT	
V _{IORM}	Maximum working insulation voltage		560	V	
V _{PR}	Input-to-output test voltage	t = 1 s (100% production), partial discharge 5 pC	1050	V	
V_{IOTM}	Transient evenuelters	t = 60 s (qualification)	4000	\/	
	Transient overvoltage	t = 1 s (100% production)	4000	v	
\/	Indiation with an annual II	t = 60 s (qualification)	2500	\/	
V_{ISO}	Isolation voltage per UL	t = 1 s (100% production)	3000	Vrms	
R _S	Insulation resistance	V_{IO} = 500 V at T_{S}	>109	Ω	
	Pollution degree		2		

(1) Climatic Classification 40/125/21

Table 2. IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	III-a
Installation classification	Rated mains voltage ≤ 150 Vrms	I–IV
	Rated mains voltage ≤ 300 Vrms	I–III
	Rated mains voltage ≤ 400 Vrms	I–II



REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program ⁽¹⁾
File number: pending (40016131)	File number: pending (1698195)	File number: pending (E181974)

⁽¹⁾ Production tested ≥ 3000 Vrms for 1 second in accordance with UL 1577.

LIFE EXPECTANCY versus WORKING VOLTAGE

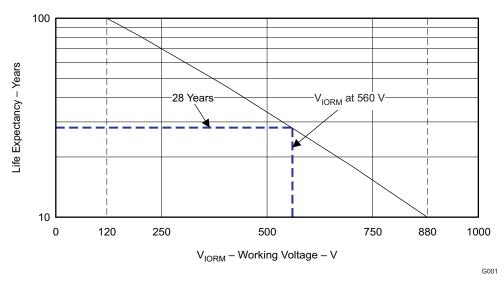


Figure 4. Life Expectancy versus Working Voltage

IEC SAFETY LIMITING VALUES

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Safety input, output, or supply	$\theta_{JA} = 212^{\circ}\text{C/W}, \ V_I = 5.5 \ \text{V}, \ T_J = 170^{\circ}\text{C}, \ T_A = 25^{\circ}\text{C}$			112	m ^
IS	current	$\theta_{JA} = 212^{\circ}\text{C/W}, \ V_{I} = 3.6 \ \text{V}, \ T_{J} = 170^{\circ}\text{C}, \ T_{A} = 25^{\circ}\text{C}$			171	mA
Ts	Maximum case temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the *Absolute Maximum Ratings* table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Characteristics* table is that of a device installed in the JESD51-3, Low-Effective-Thermal-Conductivity Test Board for Leaded Surface-Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.



PACKAGE THERMAL CHARACTERISTICS

(over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
0	Junction-to-air thermal resistance	Low-K thermal resistance ⁽¹⁾		212		°C/W
θ_{JA}	Junction-to-air thermal resistance	High-K thermal resistance ⁽¹⁾		122		C/VV
θ_{JB}	Junction-to-board thermal resistance			37		°C/W
θ_{JC}	Junction-to-case thermal resistance			69.1		°C/W
P_D	Device power dissipation	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C}, C_L = 15 \text{ pF},$ Input a 150-Mbps 50% duty-cycle square wave			390	mW

(1) Tested in accordance with the low-K or high-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages

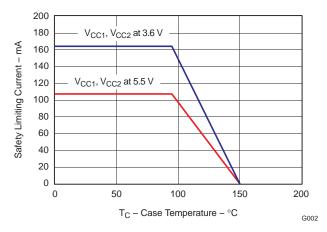


Figure 5. θ_{JC} Thermal Derating Curve per IEC 60747-5-2

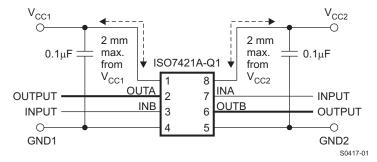


Figure 6. Typical ISO7421A-Q1 Application Circuit



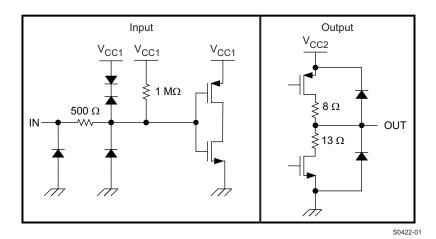
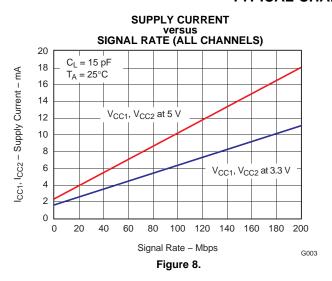
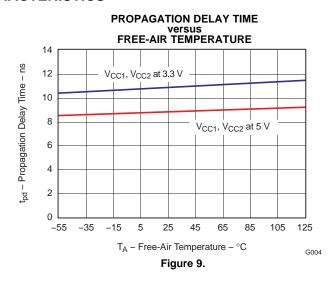


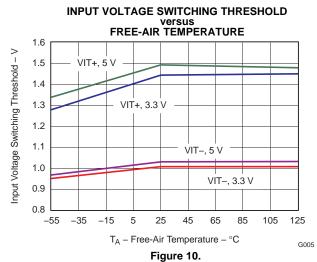
Figure 7. Device I/O Schematics

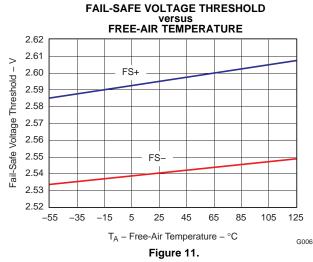
TEXAS INSTRUMENTS

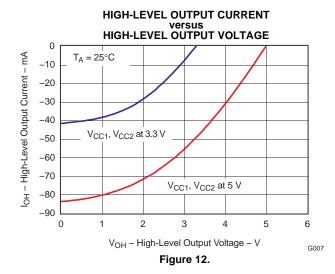
TYPICAL CHARACTERISTICS

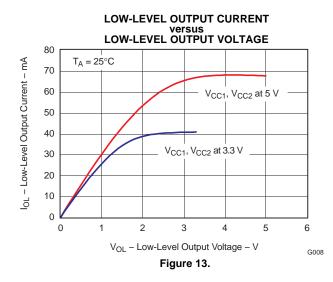






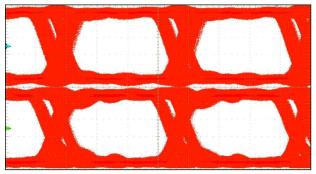








TYPICAL CHARACTERISTICS (continued)





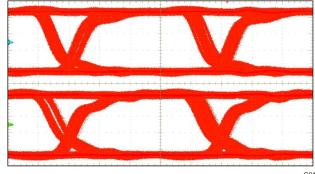


Figure 15. Eye Diagram at 200 MBPS, 5-V $\rm V_{CC},\,125^{\circ}C^{0010}$



REVISION HISTORY

	hanges from Revision A (September 2012) to Revision B	Page
•	Deleted ISO7420-Q1 part number from header of every page	1
•	Deleted ISO7420-Q1package from pinout drawing	1
•	Deleted ISO7420-Q1 part number from Description sectoin	1
•	Deleted ISO7420-Q1 from Ordering Information table	1
•	Deleted ISO7420-Q1 from Pin Functions table	2
•	Deleted ISO7420-Q1 from Supply Current section of 5-V, 5-V Electrical Characteristics table	3
•	Deleted ISO7420-Q1 from Supply Current section of 5-V, 3.3-V Electrical Characteristics table	4
•		5
•	Deleted ISO7420-Q1 from Supply Current section of 3.3-V, 5-V Electrical Characteristics table	5
•	Deleted ISO7420-Q1 from Supply Current section of 3.3-V, 5-V Electrical Characteristics table	6
•	Corrected part number in Typical Application Circuit diagram	10
•	hanges from Original (March, 2012) to Revision A	Page
	Changed High Signaling Rate from 1 to 50 Mbps.	
•	Changed High Signaling Rate from 1 to 50 Mbps. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1.	1
•	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1.	1
	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value	3
•	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1. Changed Signaling rate max value from 1 to 50. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value	3
•	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1. Changed Signaling rate max value from 1 to 50. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1 and 5.5 changed to 5.8.	
•	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1. Changed Signaling rate max value from 1 to 50. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1 and 5.5 changed to 5.8. Changed Signaling rate from 1 to 50 Mbps. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value	
•	Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1. Changed Signaling rate max value from 1 to 50. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1 and 5.5 changed to 5.8. Changed Signaling rate from 1 to 50 Mbps. Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value changed to 5.8 and 8.5 changed to 9.1.	



PACKAGE OPTION ADDENDUM

12-Sep-2013

PACKAGING INFORMATION

Orderable Device		Package Type	Package Drawing	Pins	Package Qtv	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Diawing		Qty	(2)		(3)		(4/5)	
ISO7421AQDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	7421AQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7421AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7421AQDRQ1	SOIC	D	8	2500	367.0	367.0	35.0

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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